



INTEGRATED SILICON SOLUTION, INC.

1Gb DDR3 DRAM with Error Correcting Code (ECC)

Built-in ECC feature prevents data bit errors

MILPITAS, Calif., June 6, 2016 -- Integrated Silicon Solution, Inc. (ISSI), a leader in advanced memory solutions, today announced it has begun sampling production units of its new 1-gigabit (1Gbit) DDR3 DRAMs with ECC. The new product has an embedded Error Correcting Code (ECC), which detects and corrects bit errors on-the-fly. It requires no monitoring, nor intervention to use, yet it is backward compatible with standard DDR3. The 1Gbit DDR3 device is the IS46TR16640ED, which is organized as 64Mbx16, packaged in a 96-ball BGA, and operates at 1.5V. ISSI is also offering IS46TR81280ED, which is organized as 128Mbx8, packaged in a 78-ball BGA, and operates at 1.5V. Both are available in three automotive temperature grade options: A1, which operates over -40C to +95C; A2, which operates over -40C to +105C; and A3, which operates over -40C to +125C. This adds to the DDR3 SDRAM product family, and ISSI's extensive selection of DRAMs. Just as ISSI is doing with its other DRAM products, ISSI is able to provide the long lifecycle product support as required by customer applications in Automotive, Industrial, and other high-reliability market segments.

“Today, DDR3 is implemented in a wide range of automotive, medical, industrial, and other applications, and in many of them, there is little to no tolerance for errors. With our 1Gbit DDR3 with ECC, applications can use the DRAM just as they would use a conventional DRAM, but with significantly increased confidence,” said Chuck McLaren, Director of DRAM Marketing at ISSI.

“This addition of ECC DRAM complements our extensive line of ECC SRAMs. The ECC DRAM family is a great fit for safety-related automotive applications. We also look forward to introducing a growing offering of DRAMs with ECC in the future,” said Lyn Zastrow VP of the Automotive Business Unit at ISSI.

In addition to the new DDR3 with ECC, ISSI offers a broad line of SDR, mobile SDR/DDR, DDR, DDR2, and DDR3 products, as well as a comprehensive line of asynchronous and synchronous SRAMs with densities from 64Kb to 72Mb, 256Kb-256Mb automotive grade flash memory products, and analog & mixed signal products. And ISSI supports a range of Known Good Die (KGD) devices in its portfolio.

About Integrated Silicon Solution, Inc.

ISSI is a fabless semiconductor company that designs and markets high performance integrated circuits for the following key markets: (i) automotive, (ii) communications, (iii) industrial, medical, and Military, and (iv) digital consumer. The Company's primary products are high speed and low power SRAM and low, medium, and high density DRAM. The Company also designs and markets NOR flash Products and high performance analog and mixed signal integrated circuits. ISSI is headquartered in Silicon Valley with worldwide offices in Taiwan, Japan, Singapore, China, Europe, Hong Kong, India, and Korea. Visit our web site at <http://www.issi.com/>

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